

SPECIFICATION

Device Name : IGBT Module

Type Name : 7MBR50SB060-01

Spec. No. : MS6M 0551

Date : Jun. - 02 - 2000

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Fuji Electric Co., Ltd.
Matsumoto Factory

	DATE	NAME	APPROVED	Fuji Electric Co., Ltd.		
DRAWN	Jun. - 2 - '00	T. Kobayashi		DWG. NO.	MS6M 0551	1 / 10
CHECKED	June - 2 - 00	S. Matsu	T. Kobayashi			



Revised Records

Date	Classi- fication	Ind.	Content	Applied date	Drawn	Checked	Approved
Jun.-2-'66	enactment	—	—	Issued date	—	<i>A. Myer</i>	<i>J. Myer</i>

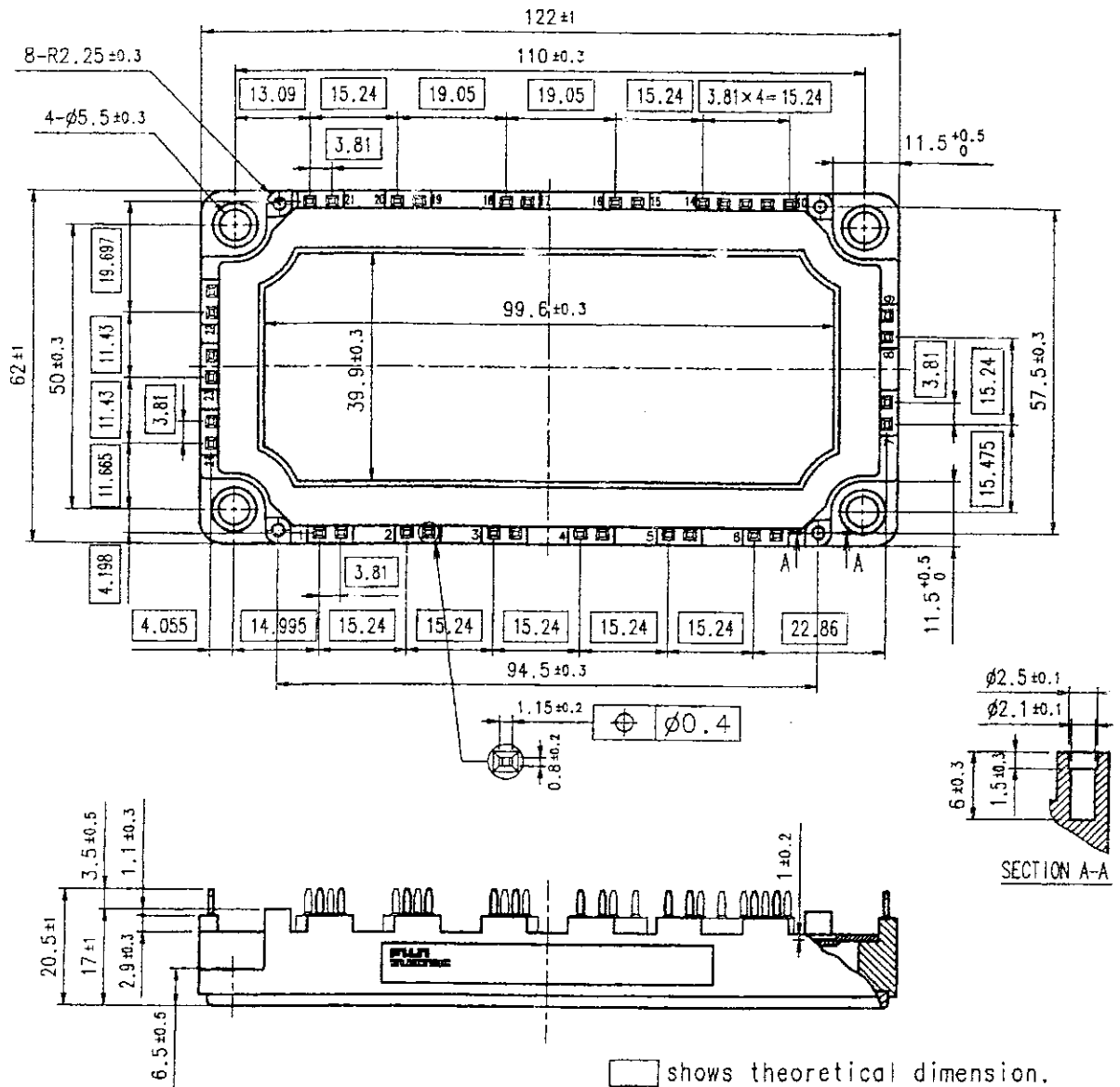
Revised Records

[illegible]

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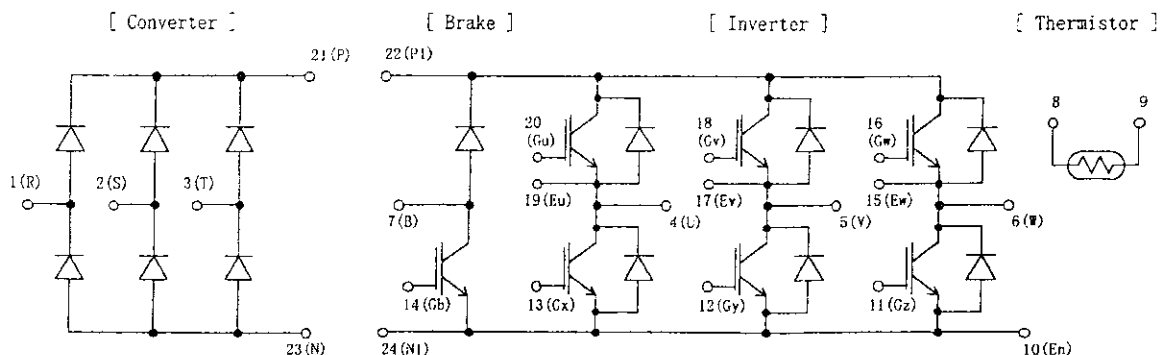
7MBR50SB060-01

1. Outline Drawing (Unit : mm)



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2. Equivalent circuit



3. Absolute Maximum Ratings (at Tc= 25C unless otherwise specified)

Items		Symbols	Conditions	Maximum Ratings	Units
Inverter	Collector-Emitter voltage	VCES		600	V
	Gate-Emitter voltage	VGES		+20	V
	Collector current	Ic	Continuous	50	A
		Icp	1ms	100	A
		-Ic		50	A
	Collector Power Dissipation	Pc	1 device	200	W
Brake	Collector-Emitter voltage	VCES		600	V
	Gate-Emitter voltage	VGES		+20	V
	Collector current	Ic	Continuous	30	A
		Icp	1ms	60	A
	Collector Power Dissipation	Pc	1 device	120	W
	Repetitive peak reverse Voltage(Diode)	VRRM		600	V
Converter	Repetitive peak reverse Voltage	VRRM		800	V
	Average Output Current	Io	50Hz/60Hz sine wave	50	A
	Surge Current (Non-Repetitive)	IFSM	Tj=150C,10ms	350	A
	I ² t (Non-Repetitive)	I ² t	half sine wave	613	A ² s
	Junction temperature	Tj		150	C
	Storage temperature	Tstg		-40~ +125	C
Isolation voltage	between terminal and copper base ^(*)	Viso	AC : 1min.	2500	V
	between thermistor and others ^(*)			2500	V
	Mounting Screw Torque ^(*)			3.5	Nm

(*)1 All terminals should be connected together when isolation test will be done.

(*)2 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

(*)3 Recommendable Value : 2.5~3.5 Nm (M5)

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4. Electrical characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

	Items	Symbols	Conditions	Characteristics			Units
				min.	typ.	Max.	
Inverter	Zero gate voltage Collector current	ICES	VGE 0 V, VCE 600 V			1.0	mA
	Gate-Emitter leakage current	IGES	VCE 0 V, VGE +20 V			200	nA
	Gate-Emitter threshold voltage	VGE(th)	VCE 20 V, Ic = 50 m	5.5	7.8	8.5	V
	Collector-Emitter saturation voltage	VCE(sat)	VGE 15 V, chip		1.8		V
			Ic = 50 A terminal		1.95	2.4	
	Input capacitance	Cies	VGE 0 V, VCE 10 V f = 1 MHz		5000		pF
	Turn-on time	ton	Vcc = 300 V		0.45	1.2	us
		tr	Ic = 50 A		0.25	0.6	
		tr0	VGE +15 V		0.08		
	Turn-off time	toff	RG = 51 ohm		0.40	1.0	
		tf			0.05	0.35	
	Forward on voltage	VF	IF = 50 A chip terminal		1.75 1.9	 2.6	V
Brake	Reverse recovery time	trr	IF = 50 A			300	ns
	Zero gate voltage Collector current	ICES	VGE 0 V, VCE 600 V			1.0	mA
	Gate-Emitter leakage current	IGES	VCE 0 V, VGE +20 V			200	nA
	Collector-Emitter saturation voltage	VCE(sat)	VGE 15 V, chip		1.8		V
			Ic = 30 A terminal		1.95	2.4	
	Turn-on time	ton	Vcc = 300 V		0.45	1.2	us
		tr	Ic = 30 A		0.25	0.6	
	Turn-off time	toff	VGE +15 V		0.40	1.0	
		tf	RG = 82 ohm		0.05	0.35	
Converter	Reverse current	IRRM	VR = 600 V			1.0	mA
	Forward on voltage	VFM	IF = 50 A chip		1.1		V
			terminal		1.2	1.5	
Thermistor	Reverse current	IRRM	VR = 800 V			1.0	mA
	Resistance	R	T = 25C		5000		ohm
			T = 100C	465	495	520	
	B value	B	T = 25/50C	3305	3375	3450	K

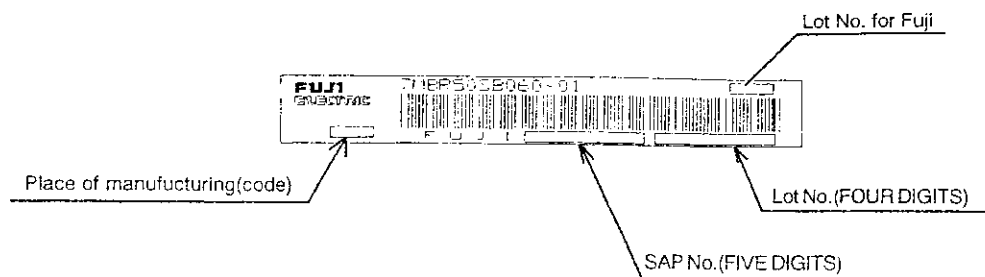
5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			0.63	C/W
		Inverter FWD			1.33	
		Brake IGBT			1.04	
		Converter Diode			0.90	
Contact Thermal resistance	Rth(c-f)	with Thermal Compound (*)		0.05		C/W

* This is the value which is defined mounting on the additional cooling fin with thermal compound.

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6. Indication on module



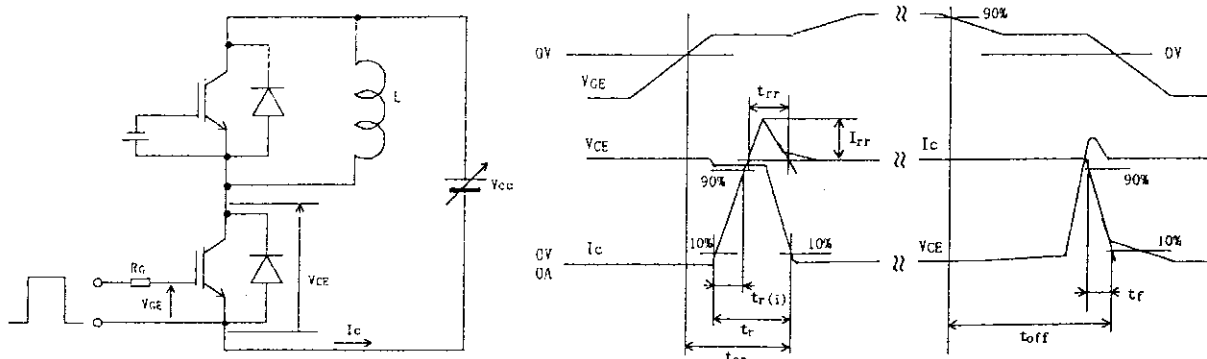
7. Applicable category

This specification is applied to Power Integrated Module named 7MBR50SB060-01.

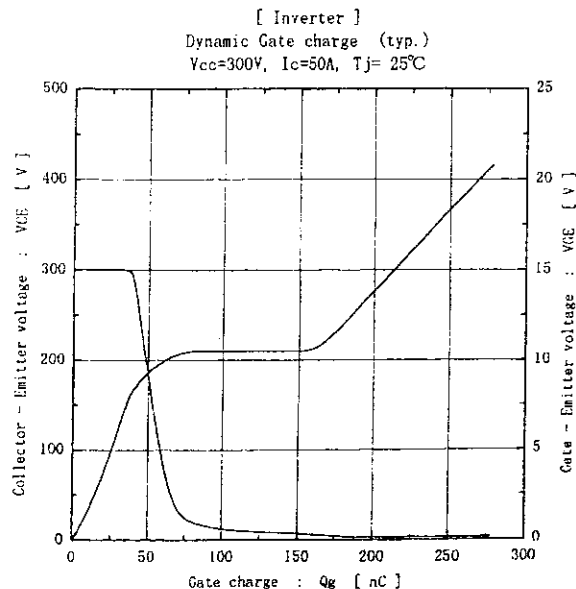
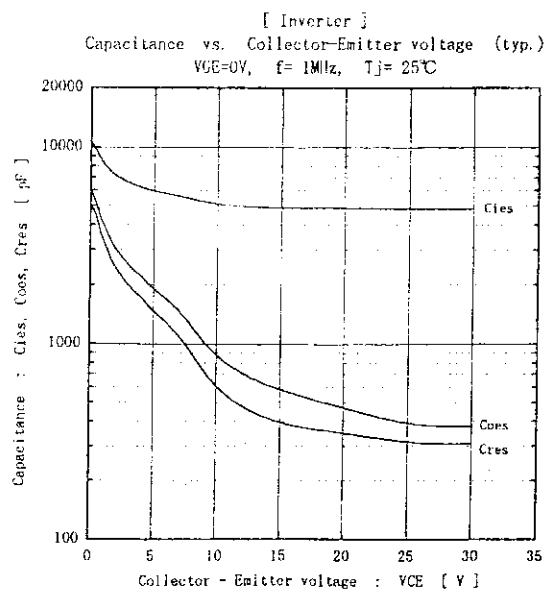
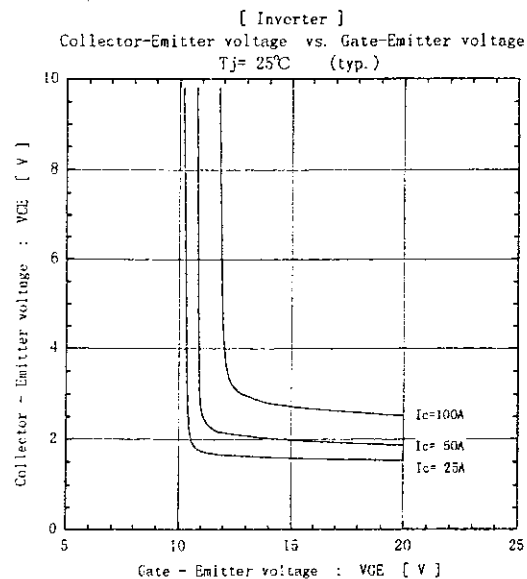
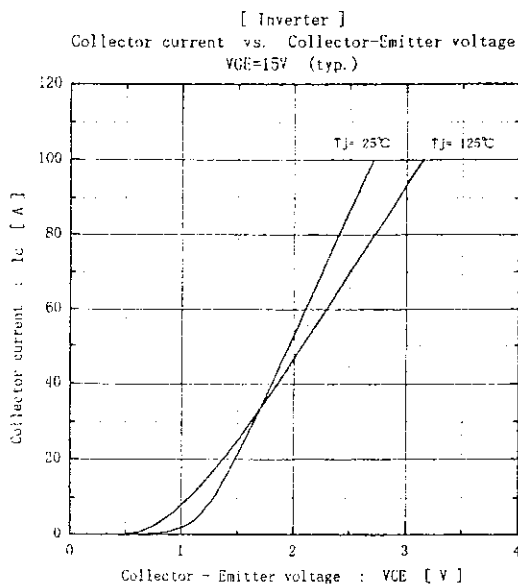
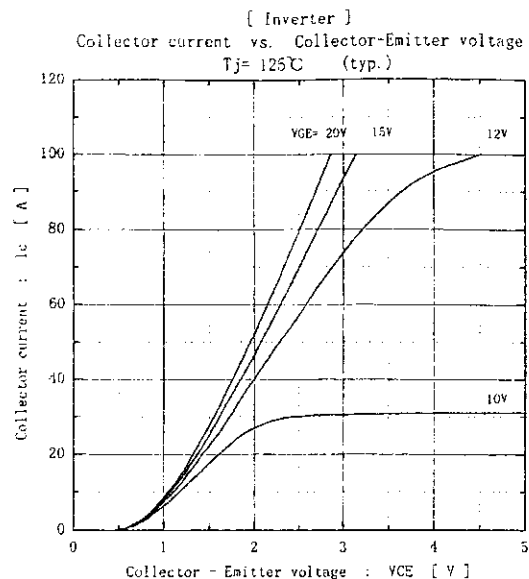
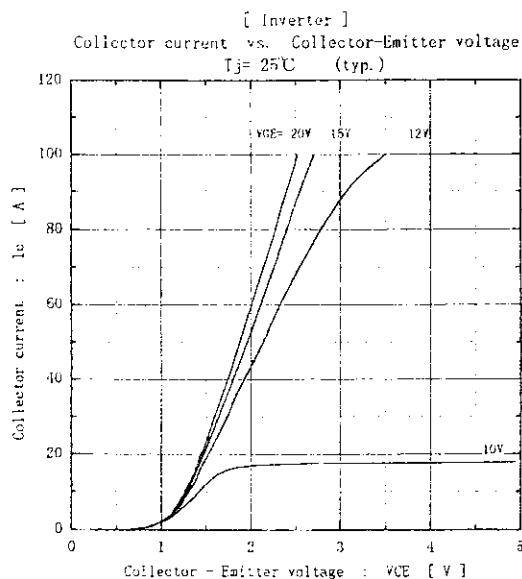
8. Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.
- Please connect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction.

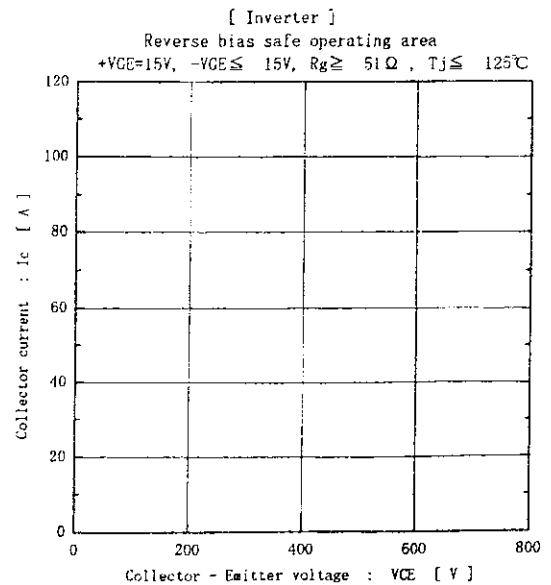
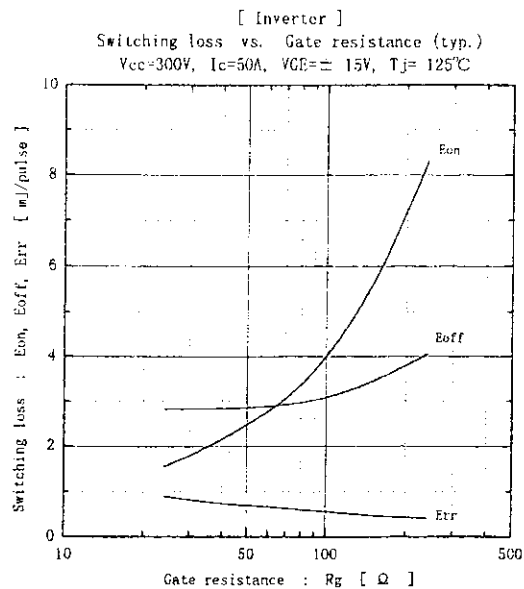
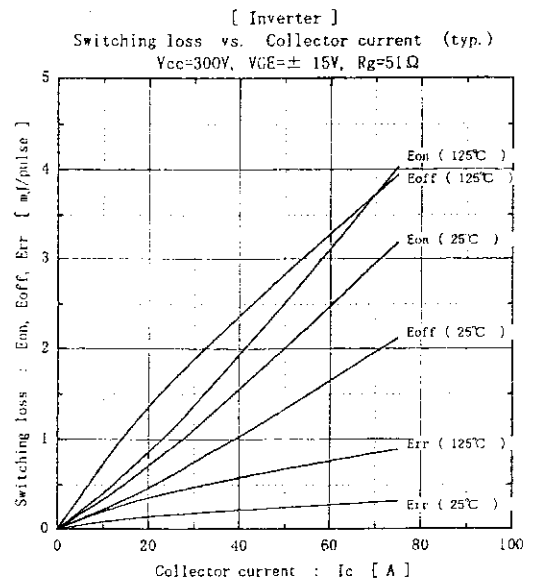
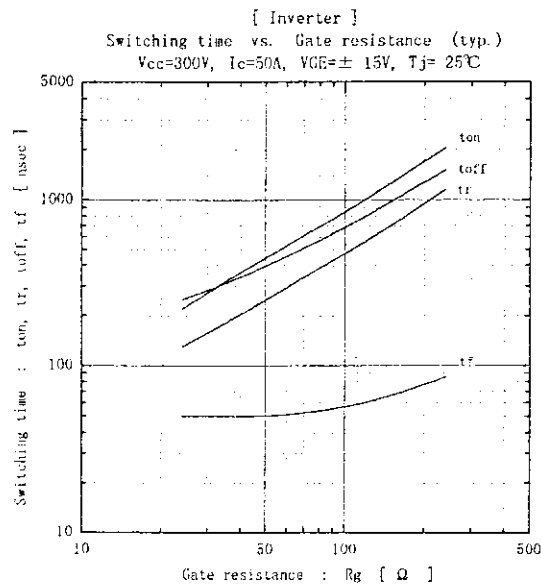
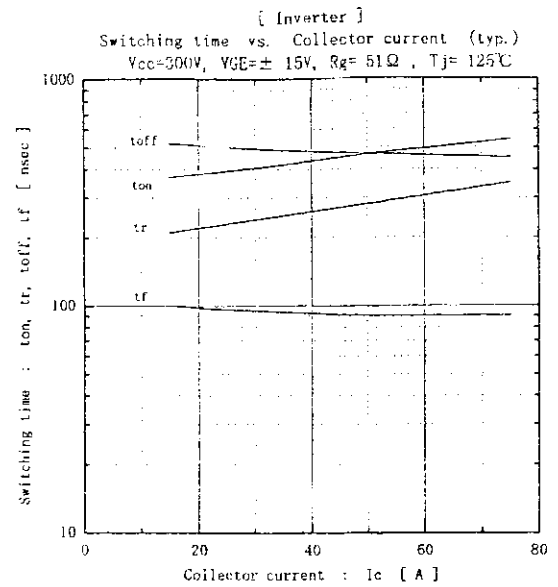
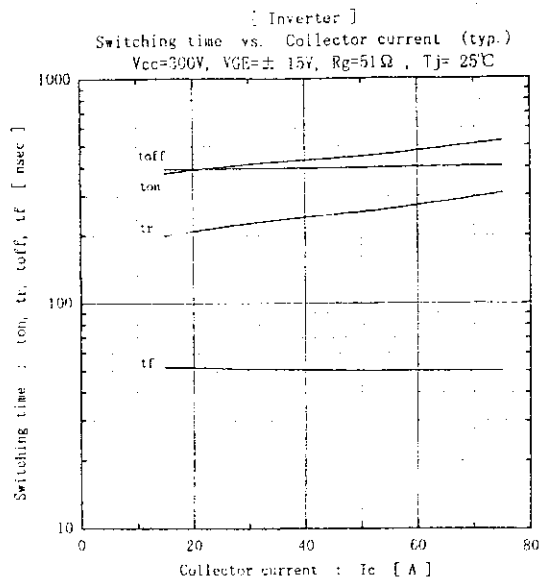
9. Definitions of switching time



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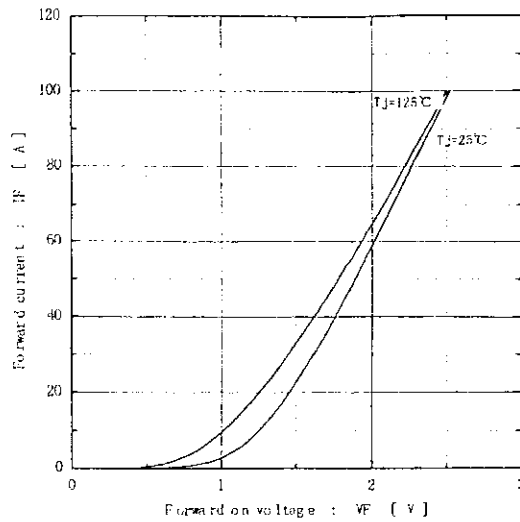


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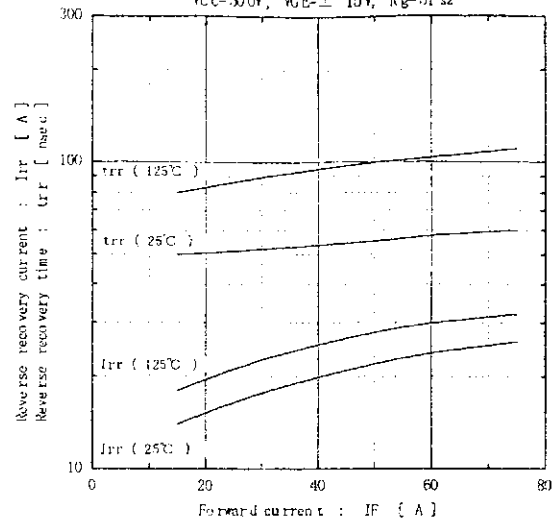


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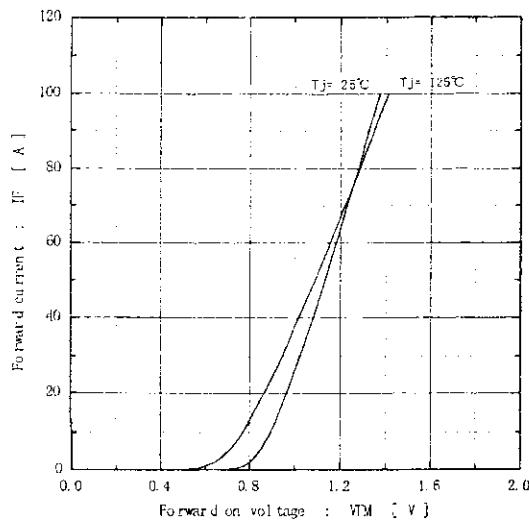
[Inverter]
Forward current vs. Forward on voltage (typ.)



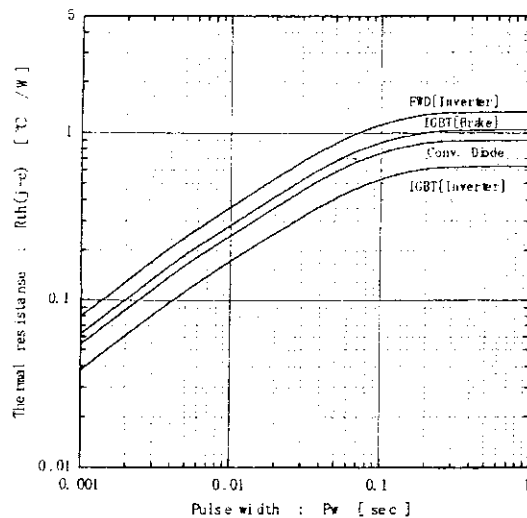
[Inverter]
Reverse recovery characteristics (typ.)
 $V_{CC}=300V$, $V_{GE}=\pm 15V$, $R_g=51\Omega$



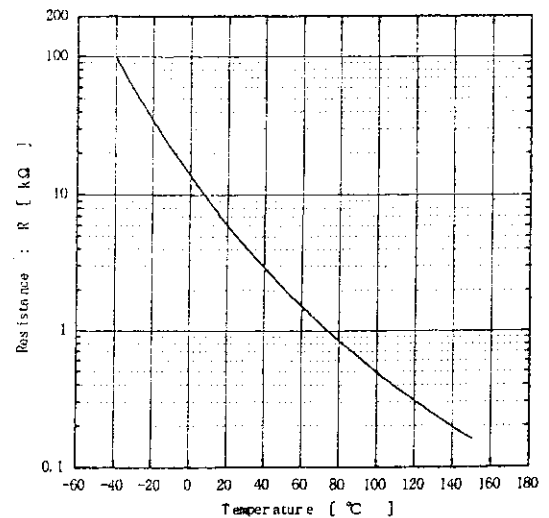
[Converter]
Forward current vs. Forward on voltage (typ.)



Transient thermal resistance



[Thermistor]
Temperature characteristic (typ.)



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